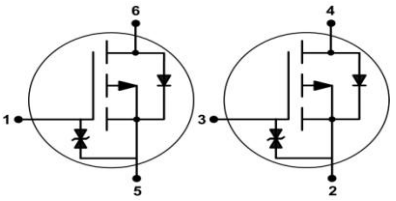
OptiMOS™ P3 Small-Signal-Transistor

Features

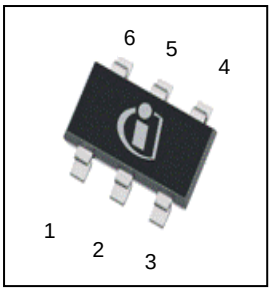
- Dual P-channel
- Enhancement mode
- Logic level (4.5V rated)
- ESD protected
- Qualified according to AEC Q101
- 100% Lead-free; RoHS compliant
- Halogen free according to IEC61249-2-21

Product Summary

V_{DS}		-30	V
$R_{DS(on),max}$	V_{GS}=-10 V	80	mΩ
	V_{GS}=-4.5 V	130	
I_D		-2.0	A



PG-TSOP-6



Type	Package	Tape and Reel Information	Marking	Lead Free	Packing
BSL308PE	PG-TSOP-6	H6327: 3000 pcs/ reel	sPR	Yes	Non dry

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter[1)]	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C	-2.0	A
		T_A=70 °C	-1.6	
Pulsed drain current	$I_{D,pulse}$	T_A=25 °C	-8.0	
Avalanche energy, single pulse	E_{AS}	I_D=-2 A, R_{GS}=25 Ω	-10.7	mJ
Reverse diode dv/dt	dv/dt	I_D=-2 A, V_{DS}=-16V, di/dt=-200A/µs, $T_{j,max}$=150 °C	6	kV/µs
Gate source voltage	V_{GS}		±20	V
Power dissipation[2)]	P_{tot}	T_A=25 °C	0.5	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
ESD Class		JESD22-A114 -HBM	2 (2kV to 4kV)	
Soldering Temperature			260 °C	°C
IEC climatic category; DIN IEC 68-1			55/150/56	°C

[1)] Only one of both transistors in operation

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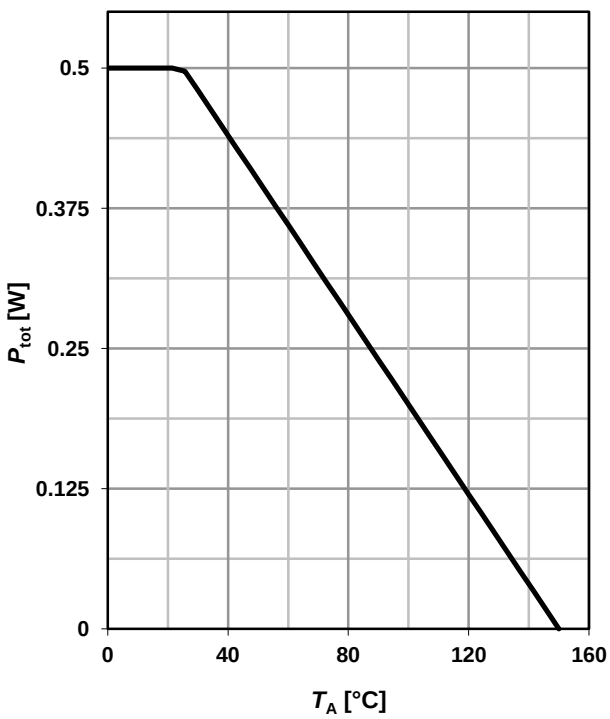
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint[2)]	-	-	250	K/W
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}= 0V, I_D=-250µA	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-11µA	-2.0	-1.5	-1.0	
Drain-source leakage current	I_{DSS}	V_{DS}=-30V, V_{GS}=0 V, T_j=25 °C	-	-	-1	µA
		V_{DS}=-30V, V_{GS}=0V, T_j=150 °C	-	-	-100	
Gate-source leakage current	I_{GSS}	V_{GS}=-20V, V_{DS}=0V	-	-	-5	µA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=-4.5 V, I_D=-1.7 A	-	88	130	mΩ
		V_{GS}=-10 V, I_D=-2 A	-	62	80	
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=-1.6 A		4.6	-	S

[2)] Performed on 40mm^2 FR4 PCB. The traces are 1mm wide, 70µm thick and 20mm long; they are present on both sides of the PCB.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=-15 V, f=1 MHz	-	376	500	pF
Output capacitance	C_{oss}		-	196	261	
Reverse transfer capacitance	C_{rss}		-	12	18	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-15V, V_{GS}=-10 V, I_D=-2 A, $R_{G,ext}$=6 Ω	-	5.6	-	ns
Rise time	t_r		-	7.7	-	
Turn-off delay time	$t_{d(off)}$		-	15.3	-	
Fall time	t_f		-	2.8	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=-15 V, I_D=-2 A, V_{GS}=0 to -10 V	-	-1.2	-	nC
Gate to drain charge	Q_{gd}		-	-0.6	-	
Gate charge total	Q_g		-	-5.0	-	
Gate plateau voltage	$V_{plateau}$		-	-3.1	-	V
Reverse Diode						
Diode continous forward current	I_S	T_A=25 °C	-	-	-0.4	A
Diode pulse current	$I_{S,pulse}$		-	-	-8.4	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=-2 A, T_j=25 °C	-	-0.8	-1.1	V
Reverse recovery time	t_{rr}	V_R=-10 V, I_F=-2 A, di_F/dt=100 A/µs	-	14	-	ns
Reverse recovery charge	Q_{rr}		-	-5.9	-	nC

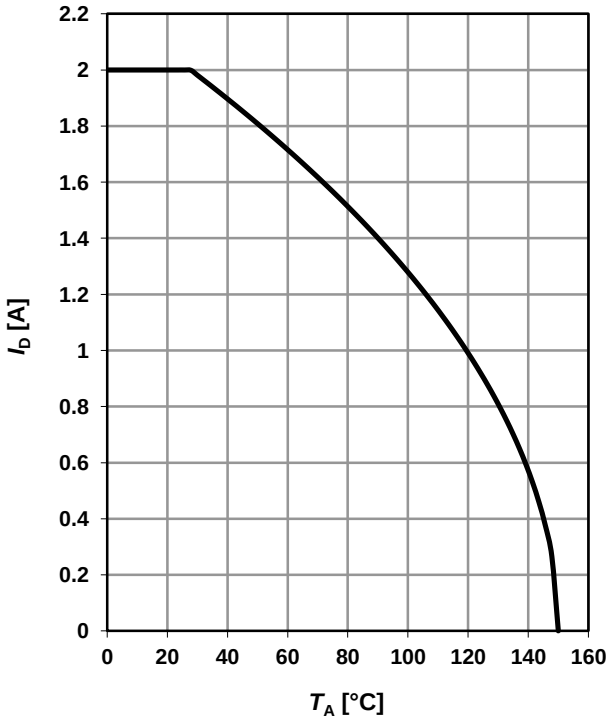
1 Power dissipation

P_{tot}=f(T_A)



2 Drain current

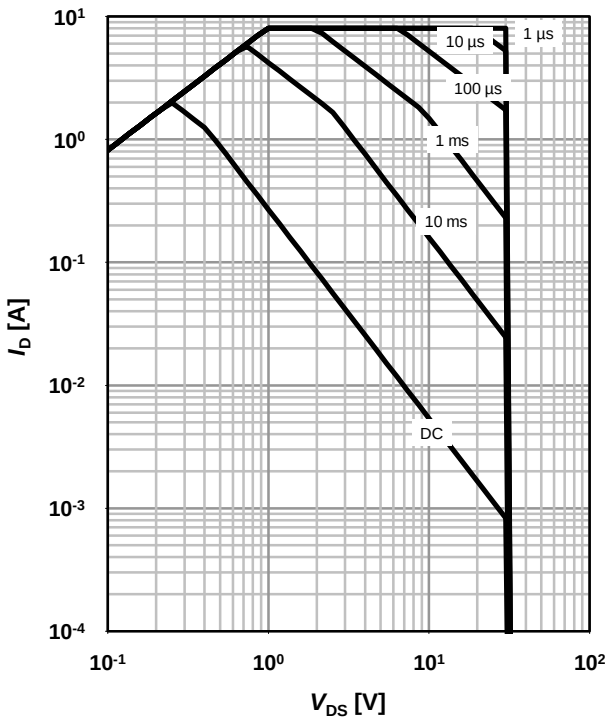
I_D=f(T_A); V_{GS}≥-10 V



3 Safe operating area

I_D=f(V_{DS}); T_A=25 °C; D=0

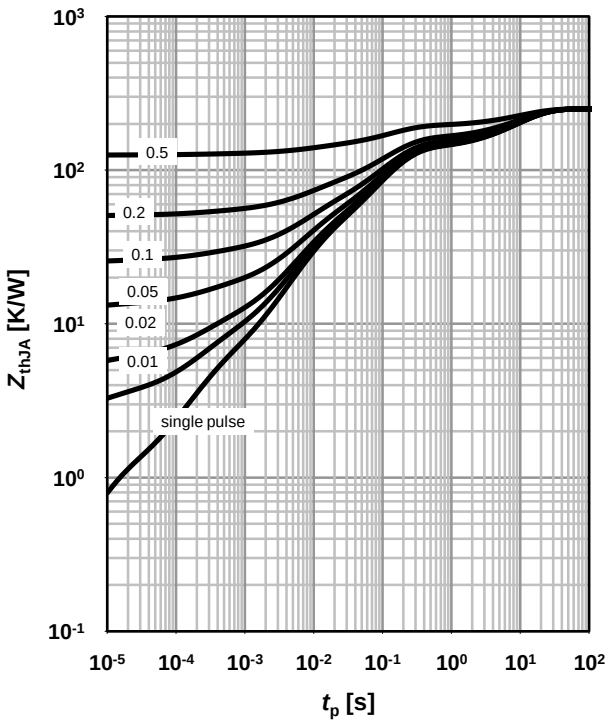
parameter: t_p



4 Max. transient thermal impedance

Z_{thJA}=f(t_p)

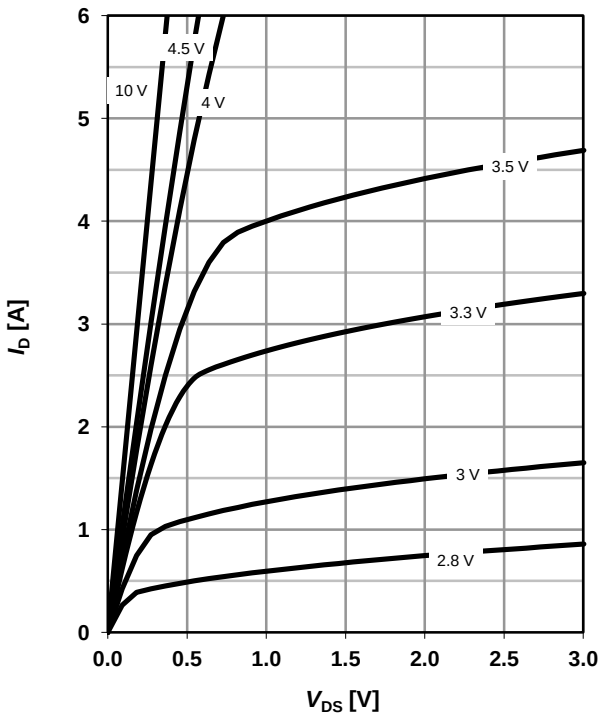
parameter: D=t_p/T



5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

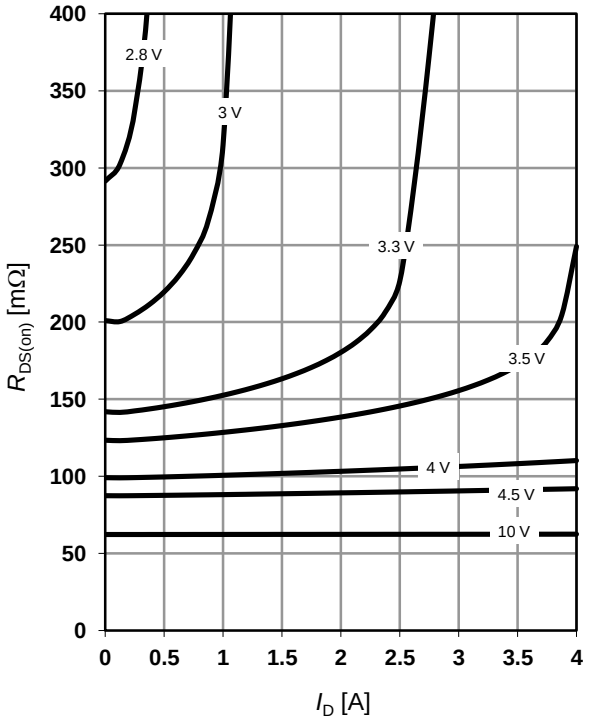
parameter: V_{GS}



6 Typ. drain-source on resistance

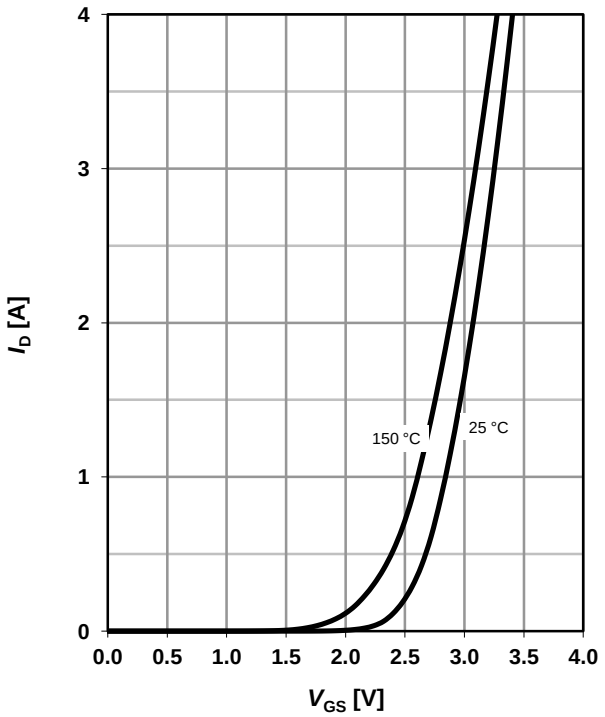
$R_{DS(on)}$=f(I_D); T_j=25 °C

parameter: V_{GS}



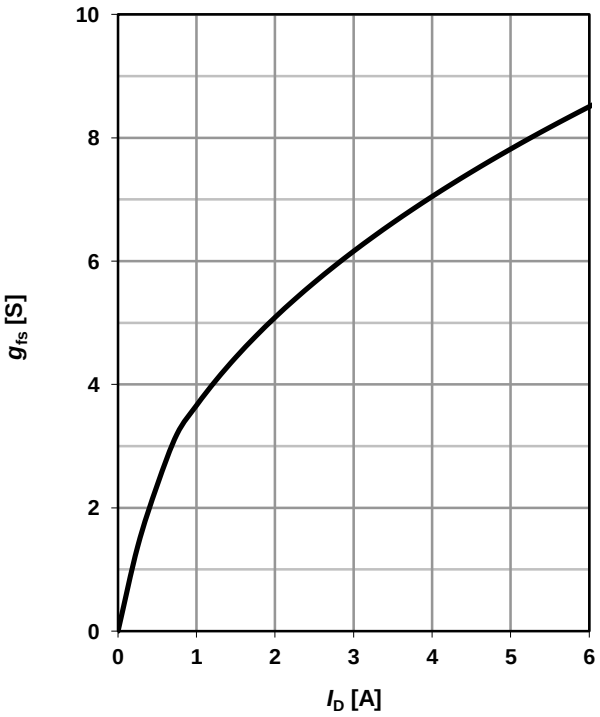
7 Typ. transfer characteristics

I_D=f(V_{GS}); |V_{DS}|>2|I_D|$R_{DS(on)max}$



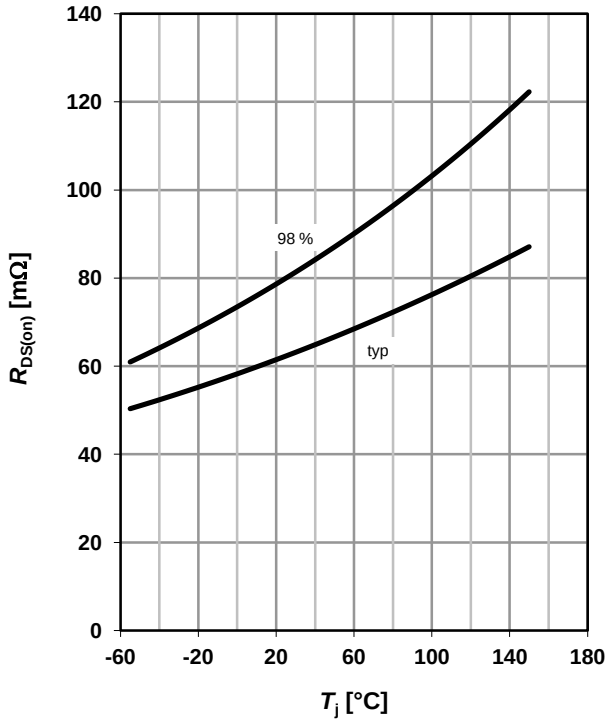
8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C



9 Drain-source on-state resistance

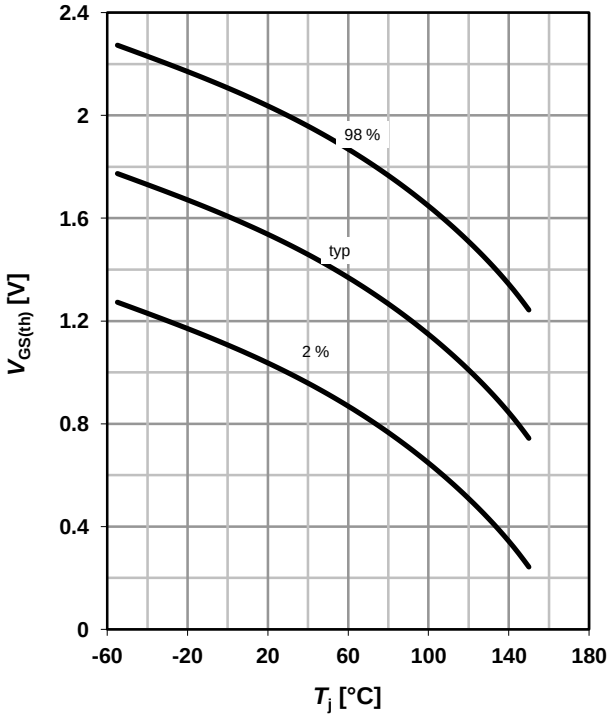
$R_{DS(on)}$=f(T_j); I_D=-2 A; V_{GS}=-10 V



10 Typ. gate threshold voltage

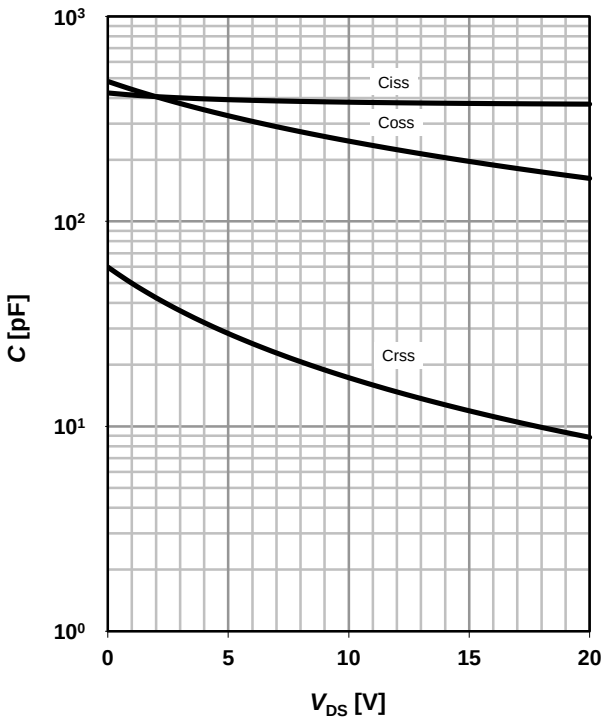
$V_{GS(th)}$=f(T_j); V_{DS}=V_{GS}; I_D=11 µA

parameter: I_D



11 Typ. capacitances

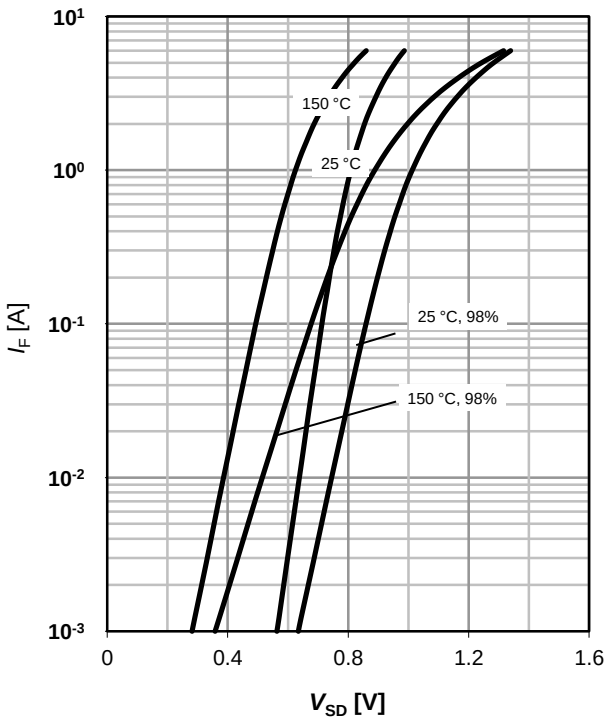
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz; T_j=25°C



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

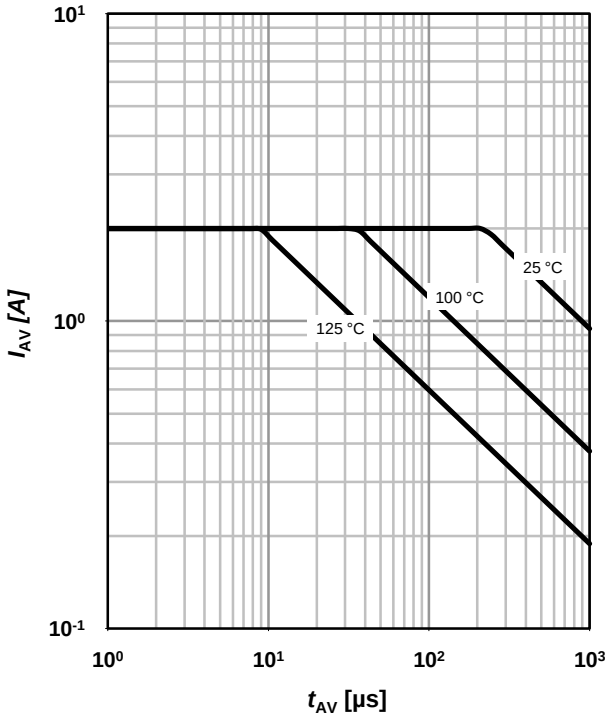
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

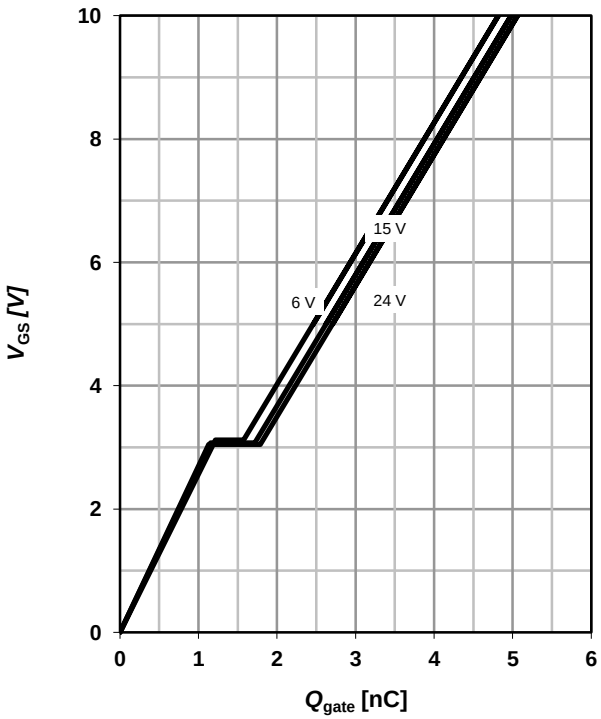
parameter: $T_{j(start)}$



14 Typ. gate charge

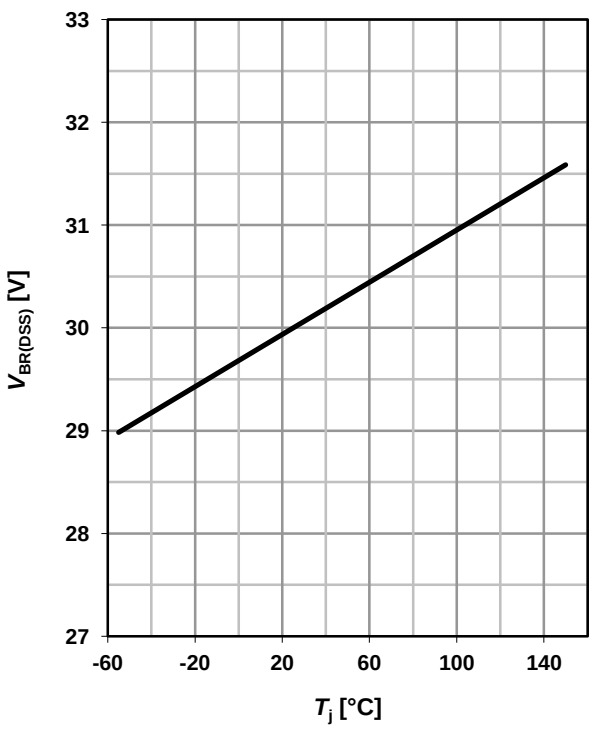
V_{GS}=f(Q_{gate}); I_D=-2 A pulsed

parameter: V_{DD}

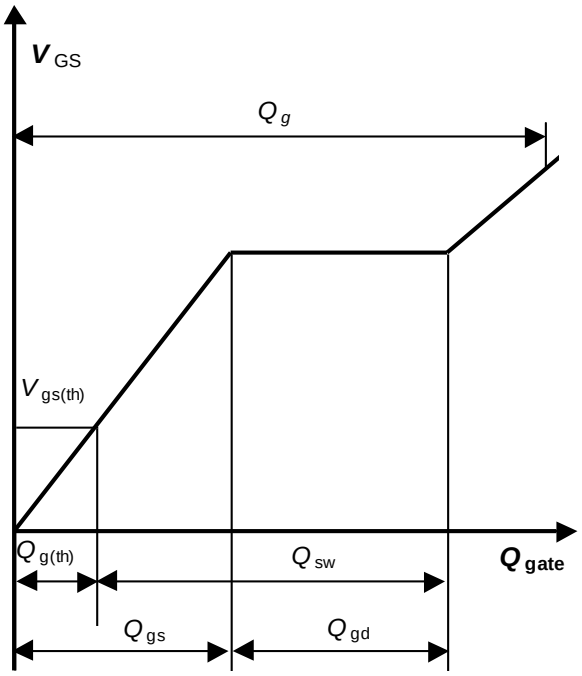


15 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=250 µA

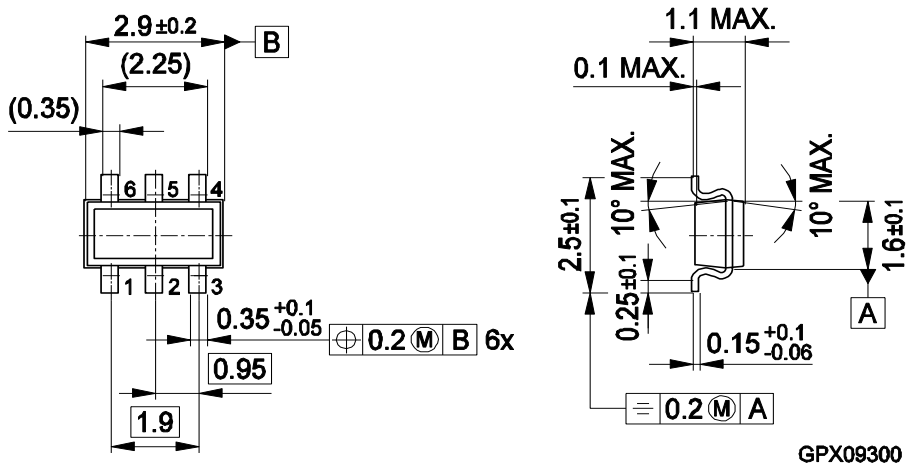


16 Gate charge waveforms

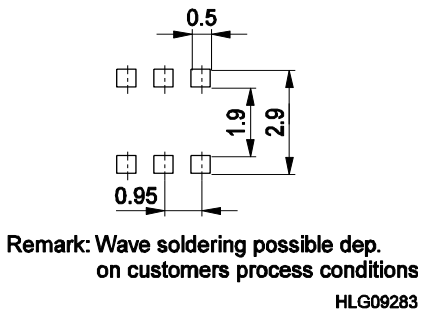


TSOP-6

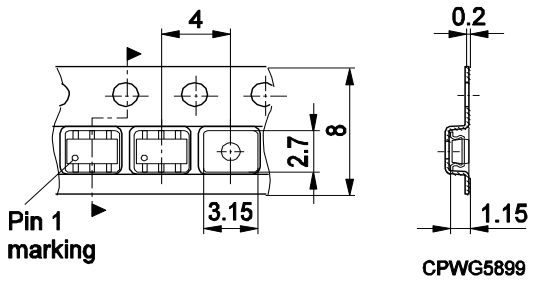
Package Outline:



Footprint:



Packaging:



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